

Title (en)

CURRENT-LIMITING SEMICONDUCTOR ARRANGEMENT

Title (de)

HALBLEITERANORDNUNGEN ZUR STROMBEGRENZUNG

Title (fr)

DISPOSITIF A SEMI-CONDUCTEUR POUR LIMITATION DE COURANT

Publication

EP 0868750 A1 19981007 (DE)

Application

EP 96946175 A 19961206

Priority

- DE 9602347 W 19961206
- DE 19548443 A 19951222

Abstract (en)

[origin: DE19548443A1] The semiconductor arrangement comprises a lateral channel region (22) and an adjacent vertical channel region (29) in a first n-conductive semiconductor region. Both channel regions are bounded by the depletion zone (23) of a p-n transition formed between the first semiconductor region (2) and a p-conductive second semiconductor region buried in the first.

IPC 1-7

H01L 29/772; **H01L 29/86**

IPC 8 full level

H01L 29/861 (2006.01); **F16L 3/08** (2006.01); **H01L 29/10** (2006.01); **H01L 29/80** (2006.01); **H01L 29/808** (2006.01); **H01L 29/812** (2006.01)

CPC (source: EP US)

H01L 29/1066 (2013.01 - EP US); **H01L 29/8083** (2013.01 - EP US); **H01L 29/8122** (2013.01 - EP US)

Citation (search report)

See references of WO 9723911A1

Cited by

US9209318B2; US9666696B2

Designated contracting state (EPC)

CH DE FR GB IT LI SE

DOCDB simple family (publication)

DE 19548443 A1 19970626; CN 1147000 C 20040421; CN 1205802 A 19990120; DE 59610316 D1 20030508; EP 0868750 A1 19981007; EP 0868750 B1 20030402; JP 2000505239 A 20000425; US 6034385 A 20000307; WO 9723911 A1 19970703

DOCDB simple family (application)

DE 19548443 A 19951222; CN 96199113 A 19961206; DE 59610316 T 19961206; DE 9602347 W 19961206; EP 96946175 A 19961206; JP 52320197 A 19961206; US 10316898 A 19980622